


FIELD-EFFECT TYPE SEMICONDUCTOR ELEMENT

Patent Number: JP8264772
Publication date: 1996-10-11
Inventor(s): KUSHIDA TOMOYOSHI; KAWAI FUMIAKI
Applicant(s): TOYOTA MOTOR CORP
Requested Patent:  JP8264772
Application Number: JP19950064545 19950323
Priority Number(s):
IPC Classification: H01L29/78
EC Classification:
Equivalents:

Abstract

PURPOSE: To make decrease of threshold voltage compatible with decrease of on-resistance, and improve punchthrough breakdown voltage, in an MOSFET.

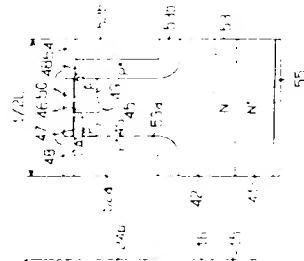
CONSTITUTION: A gate oxide film 45 is formed surrounding a gate electrode 46. A diffusion layer 49 as a low concentration layer is formed on the side part of the gate electrode 46. Diffusion layers 53a, 53b are formed on the side part of the diffusion layer 49, sufficiently deeper in the drain direction than the gate electrode 46 and the diffusion layer 49. Since the distance between the lower end portions of P<+> body layers (diffusion layers (53a, 53b) is short, depletion layers 56 between the P<+> body layers are easy to be linked together.

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【例 4】



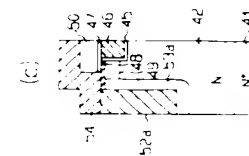
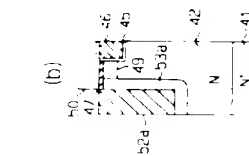
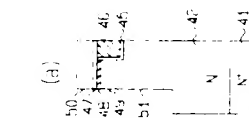
【例 5】



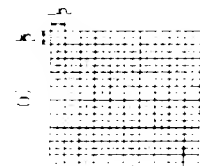
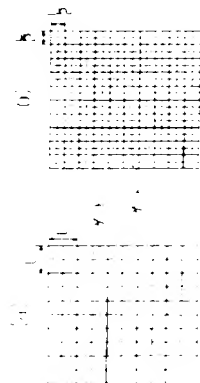
【例 7】



【例 9】



【例 6】



【例 8】

